	Туре	L #	Hits	Search Text	DBs	Tim Stamp
1	BRS	L27	832	((lower or source) adj electrode\$3) same (SiN or (Silicon adj nitride) same (TiNiAg) same PSG)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 13:40
2	BRS	L28		(((lower or source) adj electrode\$3) same (SiN or (Silicon adj nitride) same (TiNiAg) same PSG)) and ((upper or top) adj electrode\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 13:41
3	IS&R	L29	1985	(438/612).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 13:42
4	BRS	L31	22347	30 and mosfet	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 13:43
5	BRS	L32	22356	31 "TiNiAg"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 13:44

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	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L33	6	31 and "TiNiAg"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 13:46
7	BRS	L35	13	34 and (lift-off or (lift adj3 off) or (lifted adj3 off))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 14:08
8	BRS	L34	266		USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 14:31
9	BRS	L36	6838		USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 14:33
10	BRS	L37	122	36 and damascene	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08

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	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L38	2	(upper near2 electrode\$3) near8 TiNiAg	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 15:15
12	BRS	L39	218	insulating near8 (SiN or (silicon adj nitride)) near8 (PSG or phospho)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 15:17
13	BRS	L40	10	39 and damascene	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 15:19
14	BRS	L41	1418	insulat\$4 same (SiN or (silicon adj nitride)) same (PSG or phospho)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 15:20
15	BRS	L42	119	41 and damascene	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	

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	Туре	L #	Hits	Search T xt	DBs	Time Stamp
16	BRS	L43	319		USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 15:37
17	BRS	L44	2	(upper adj3 electrode) near8 TiNiAg	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 15:38
18	BRS	L45	283	insulat\$4 near8 (SiN or "silicon nitride") near8 PSG	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 15:40
19	BRS	L46	1	43 and 45	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 15:55
20	BRS	L47	67	insulating near8 SiN near8 PSG	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 16:02

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	Туре	L #	Hits	S arch Text	DBs	Time Stamp
21	BRS	L48	77		USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 16:02
22	BRS	L49	10	48 not 47	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 16:05
23	BRS	L50	3		USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 16:39
24	BRS	L51	313	insulat\$4 same (SiN) same PSG	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 16:39
25	BRS	L52	25305	electrode near8 aluminum	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 16:40

	Туре	L #	Hits	Search Text	DBs	Time Stamp
26	BRS	L56	47	51 and 52	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 16:41
27	BRS	L54	0	51 and 52 and 53	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 17:11
28	BRS	L53	41	electrode near8 (TiNiAg or (titanium near2 nickel near2 silver))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 17:12
29	IS&R	L59	1985	(438/612).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 17:56
30	BRS	L60	92	(SiN) near8 PSG near8 (insulating or insulator)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 17:59

	Туре	L #	Hits	S arch Text	DBs	Time Stamp
31	BRS	L63	14416		USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 17:59
32	BRS	L64	12	60 and 63	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 18:17
33	IS&R	L67	188	(438/615).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 18:17
34	IS&R	L68	764	(257/762).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 18:17
35	IS&R	L73	1480	(257/784).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 18:18

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	Тур	L #	Hits	Search Text	DBs	Time Stamp
36	IS&R	L74	1164	(257/763).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 18:40
37	IS&R	L75	584	(257/766).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 19:04
38	IS&R	L76	365	(257/772).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 19:11
39	IS&R	L77	806	(257/779).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 19:14
40	BRS	L78	1775	bond\$4 near2 pad near2 electrode	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/08/08 19:18